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<b>Publication number</b>	548799																												
<b>Title</b>	Method of manufacturing semiconductor device with offset sidewall structure																												
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<b>Abstract</b>	A method of manufacturing a semiconductor device with NMOS and PMOS transistors is provided. The semiconductor device can lessen a short channel effect, can reduce gate-drain current leakage, and can reduce parasitic capacitance due to gate overlaps, thereby inhibiting a reduction in the operating speed of circuits. An N-type impurity such as arsenic is ion implanted to a relatively low concentration in the surface of a silicon substrate (1) in a low-voltage NMOS region (LNR) thereby to form extension layers (61). Then, a silicon oxide film (OX2) is formed to cover the whole surface of the silicon substrate (1). The silicon oxide film (OX2) on the side surfaces of gate electrodes (51-54) is used as an offset sidewall. Then, boron is ion implanted to a relatively low concentration in the surface of the silicon substrate (1) in a low-voltage PMOS region (LPR) thereby to form P-type impurity layers (62) later to be extension layers (62).																												
<b>Patent Right Change</b>	<table border="0"> <tr> <td>Application number</td> <td>091116293</td> </tr> <tr> <td>Authorization note</td> <td>No</td> </tr> <tr> <td>Qualification right note</td> <td>No</td> </tr> <tr> <td>Transfer Note</td> <td>No</td> </tr> <tr> <td>Inheritance Note</td> <td>No</td> </tr> <tr> <td>Trust note</td> <td>No</td> </tr> <tr> <td>Objection note</td> <td>No</td> </tr> <tr> <td>Exposure Note</td> <td>No</td> </tr> <tr> <td>Invalidation date</td> <td></td> </tr> <tr> <td>Withdrawal date</td> <td></td> </tr> <tr> <td>Issue date of patent right</td> <td>20030821</td> </tr> <tr> <td>Due date of patent right</td> <td>20220721</td> </tr> <tr> <td>Due date of annual fee</td> <td>20080820</td> </tr> <tr> <td>Due year of annual fee</td> <td>005</td> </tr> </table>	Application number	091116293	Authorization note	No	Qualification right note	No	Transfer Note	No	Inheritance Note	No	Trust note	No	Objection note	No	Exposure Note	No	Invalidation date		Withdrawal date		Issue date of patent right	20030821	Due date of patent right	20220721	Due date of annual fee	20080820	Due year of annual fee	005
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